

Device Modeling Report

COMPONENTS: TRANSISTOR
PART NUMBER: 2SC5848001JN
MANUFACTURER: PANASONIC



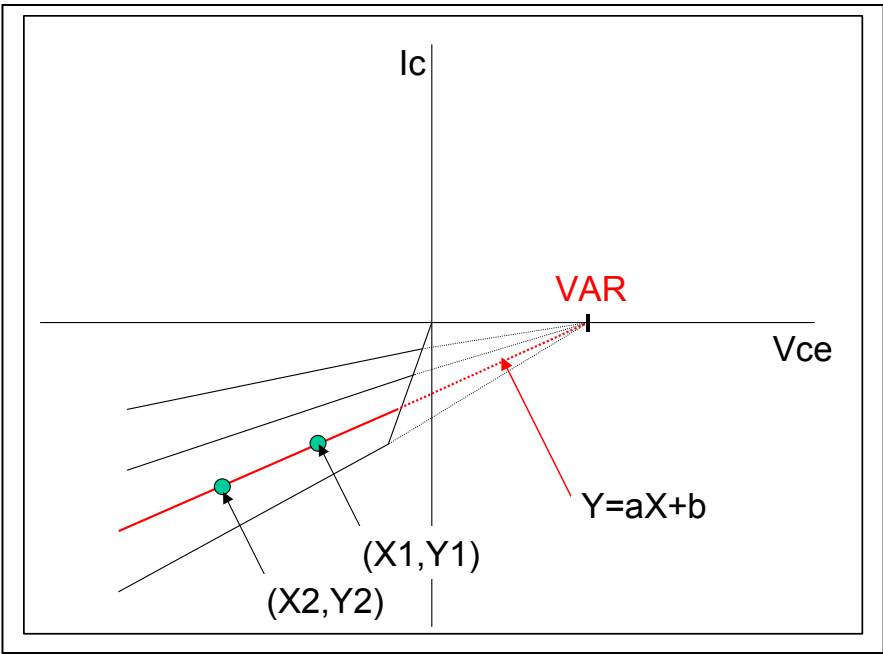
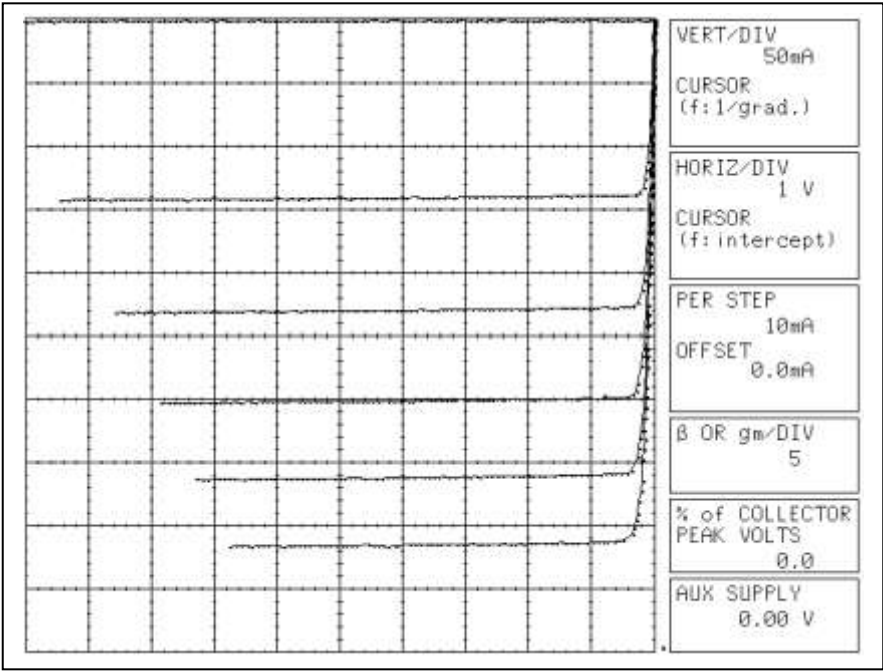
Bee Technologies Inc.

TRANSISTOR MODEL

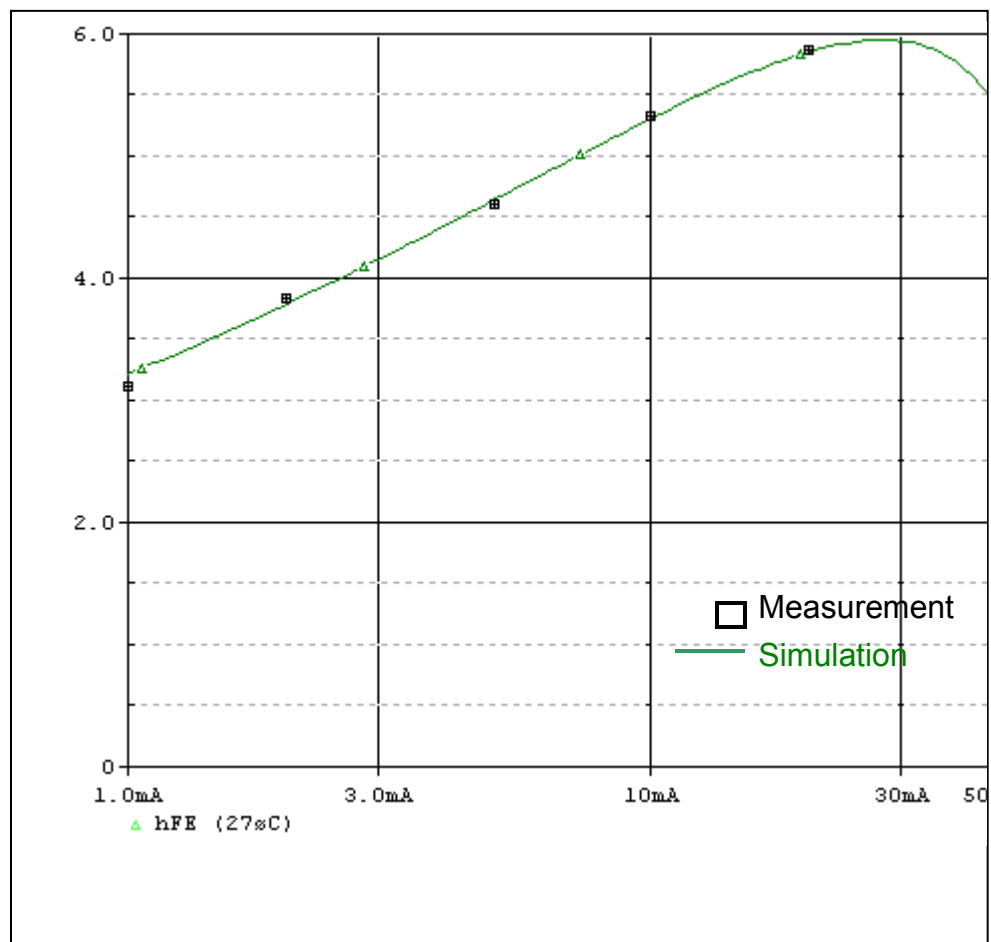
PSpice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at $f=1/2\pi \cdot TF$
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

Reverse

Reverse Early Voltage Characteristic

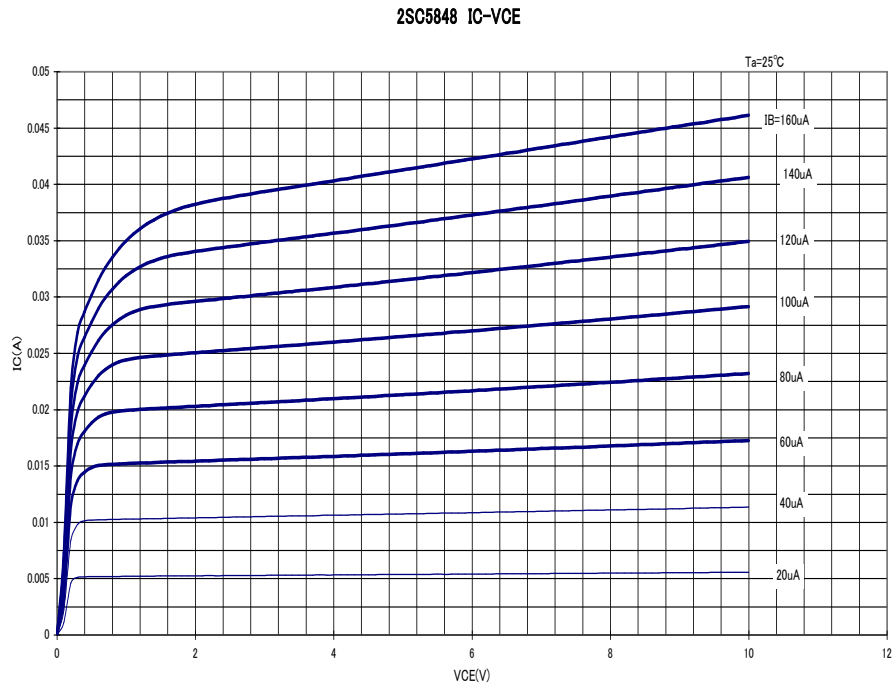


Reverse DC Beta Characteristic (I_e vs. h_{FE})

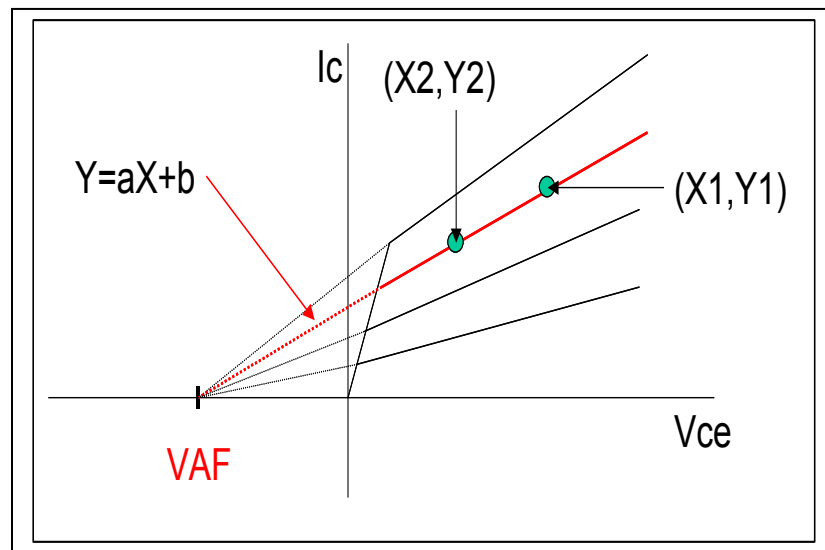


Forward

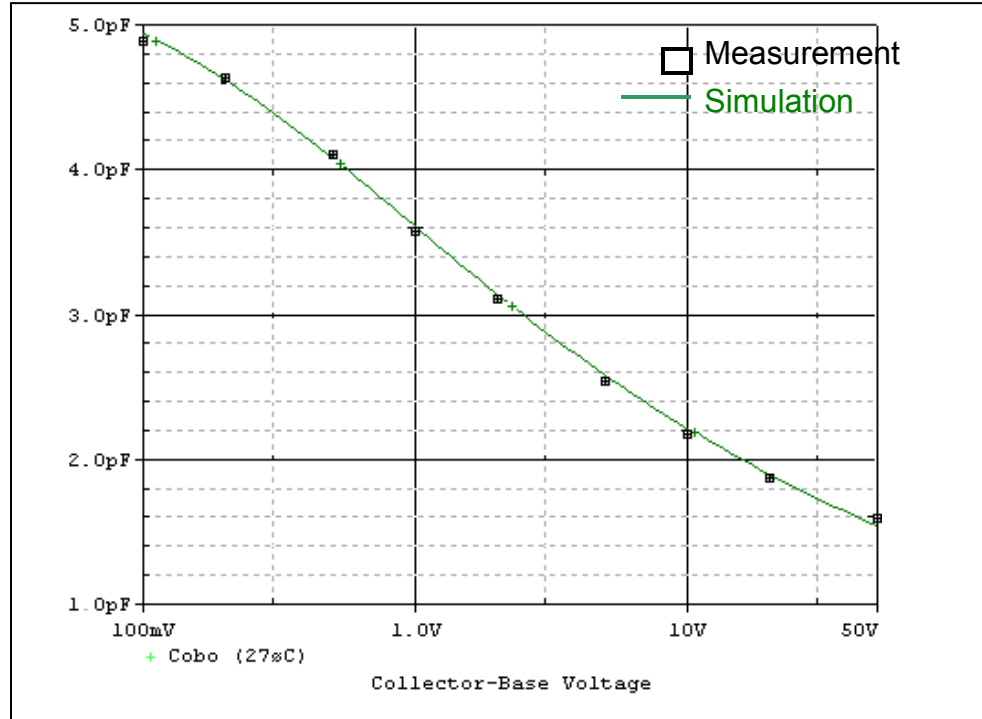
Forward Early Voltage Characteristic



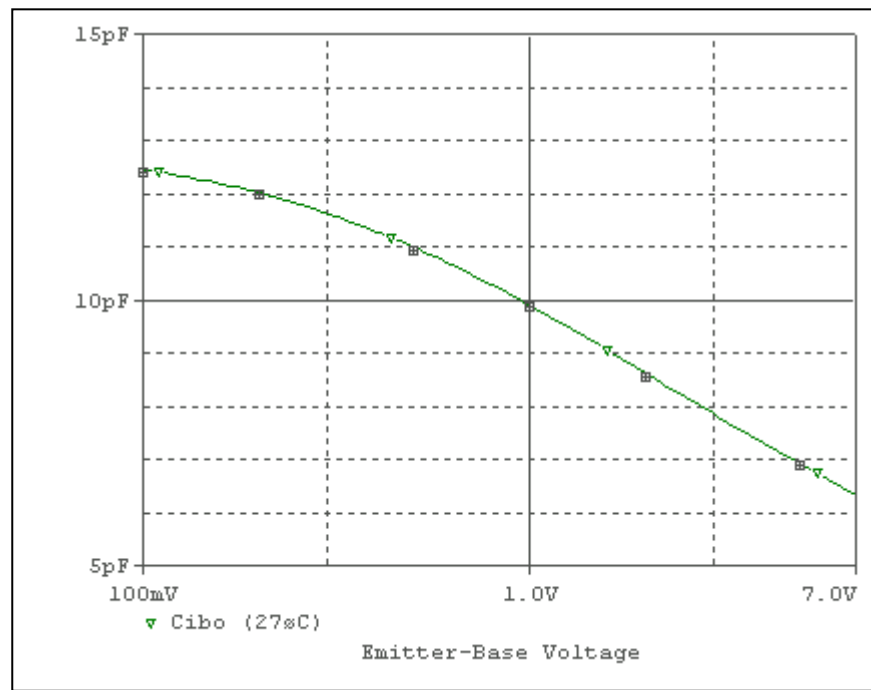
Semiconductor Company, Matsushita Electric Industrial Co., Ltd.



C-B Capacitance Characteristics

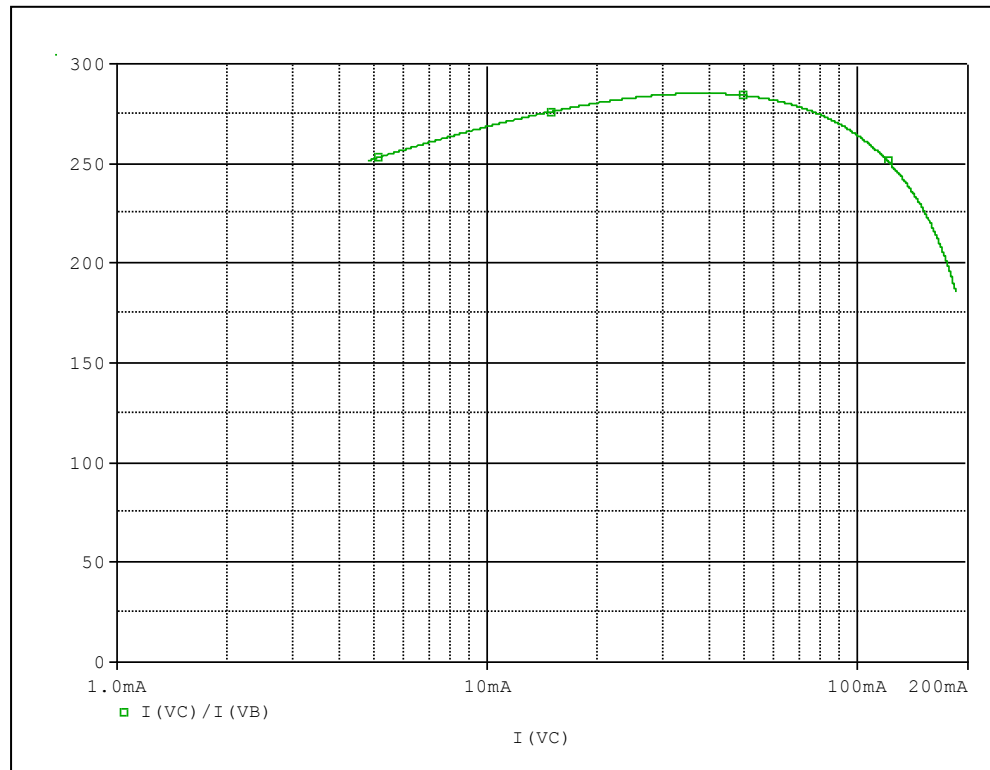


E-B Capacitance Characteristics

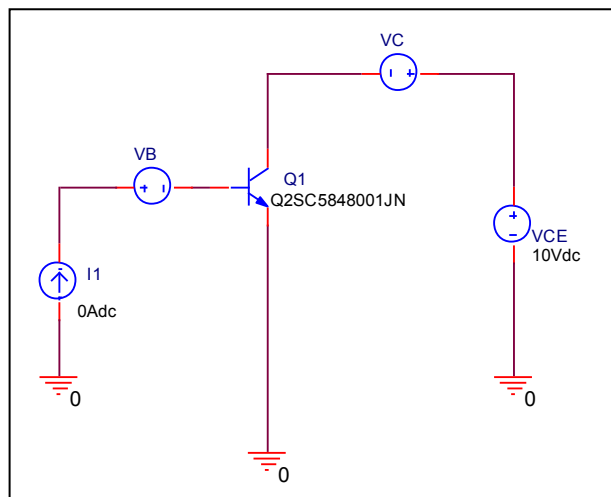


Transistor h_{FE} - I_C Characteristics

Circuit Simulation Result

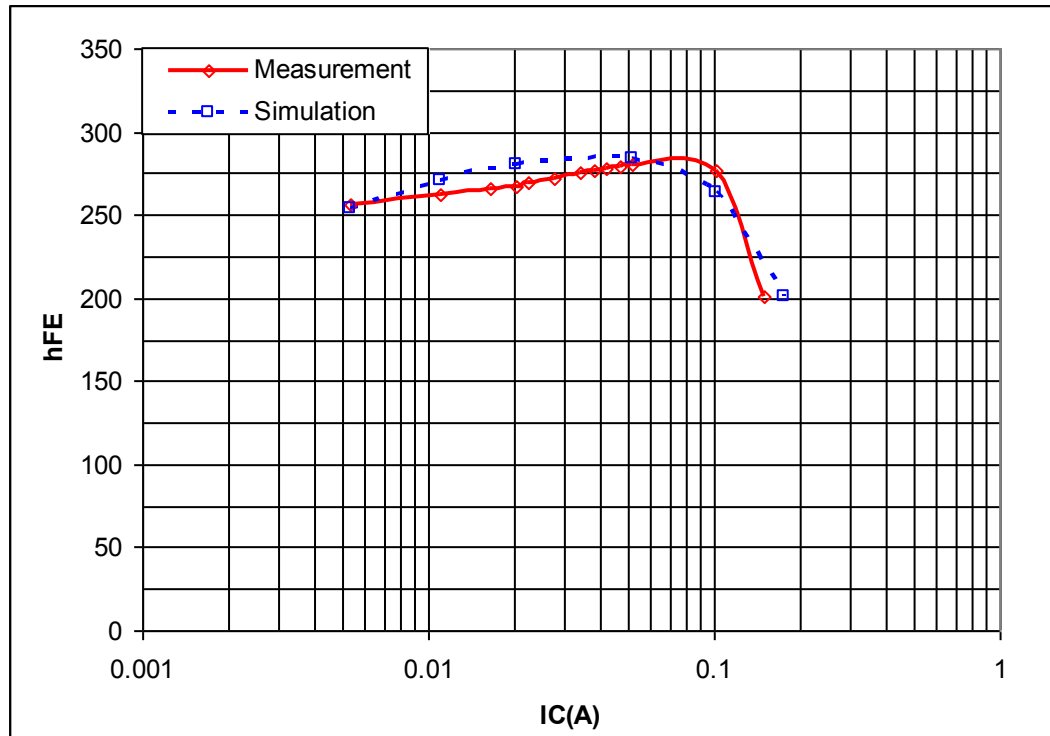


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

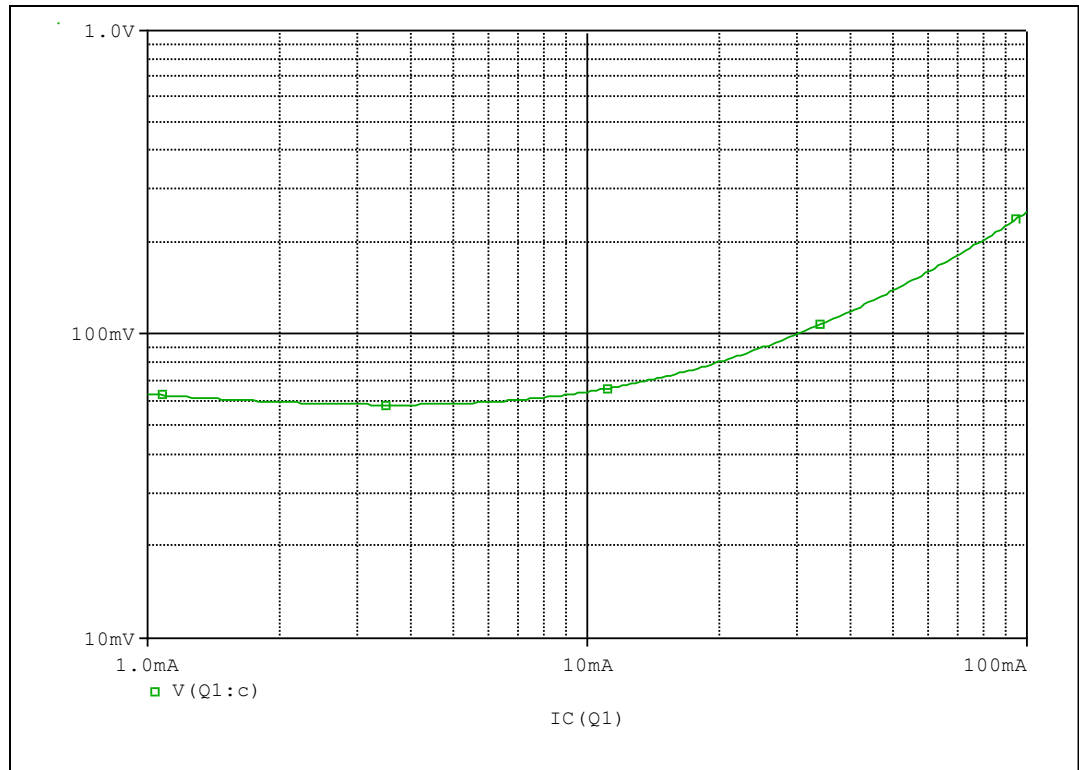


Simulation Result

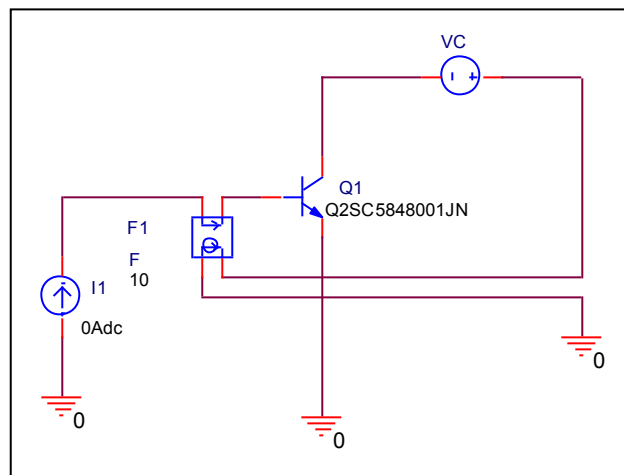
Ic(mA)	hFE		Error(%)
	Measurement	Simulation	
0.00537	256.554	254.293	-0.88
0.01095	261.668	270.289	3.29
0.0203	267.583	280.641	4.88
0.0518	280.152	283.677	1.26
0.102	276.13	263.264	-4.66

$V_{CE(Sat)}$ - I_C Characteristics

Circuit Simulation Result

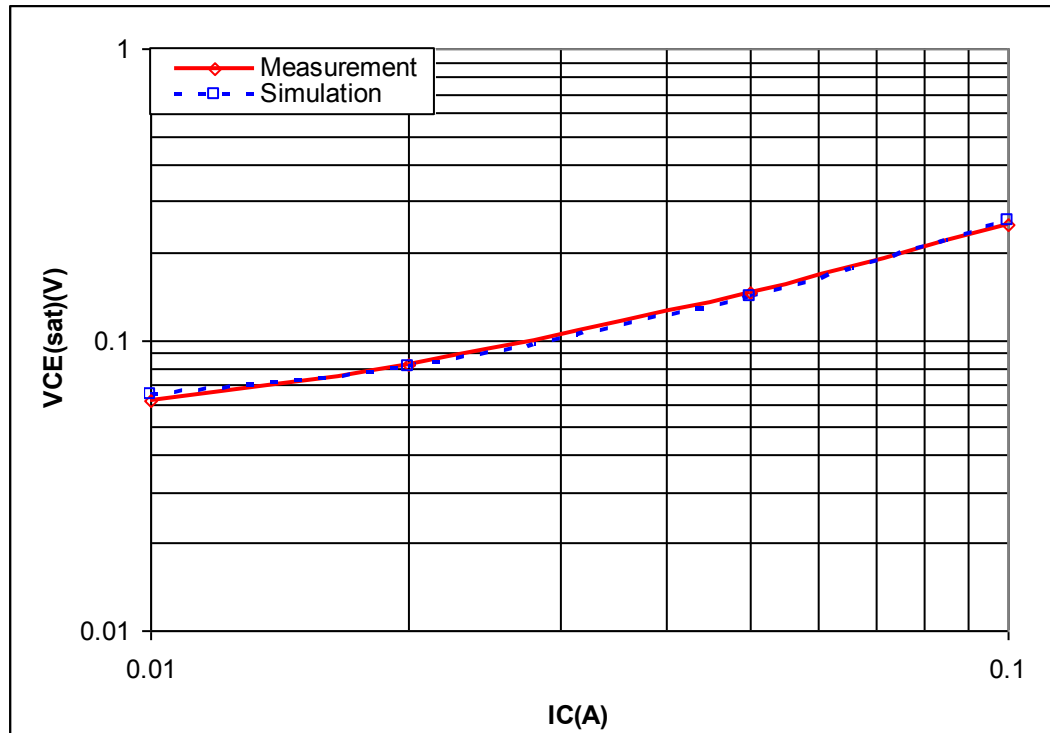


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

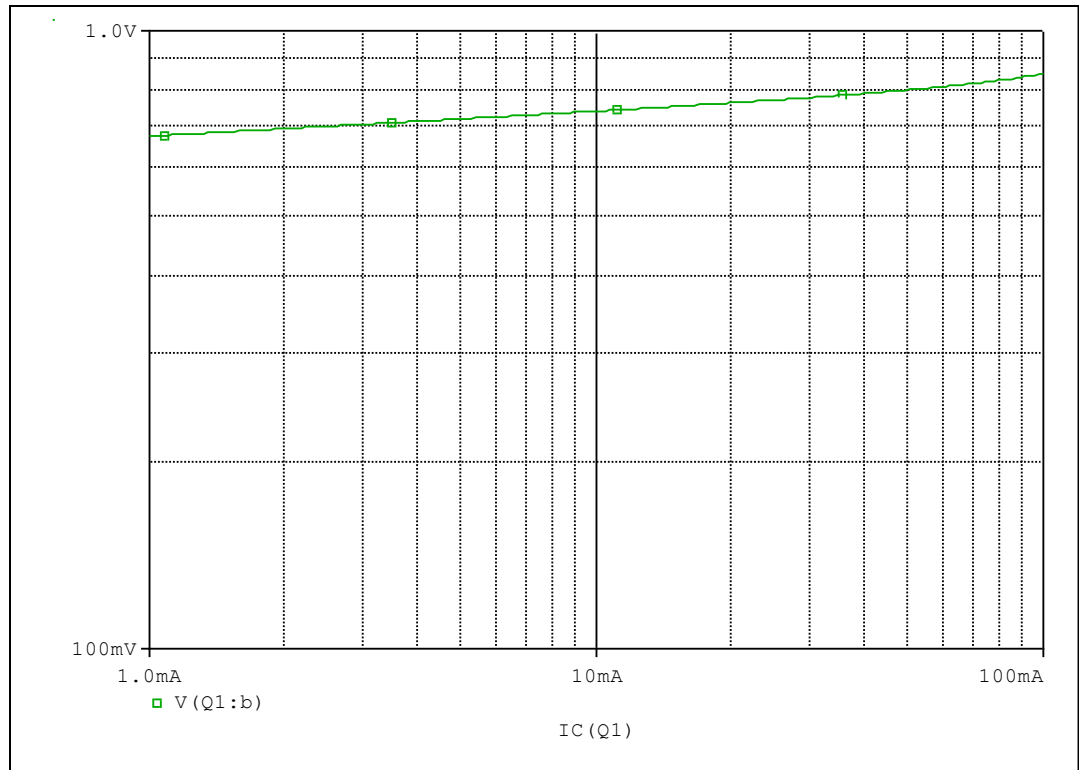


Simulation Result

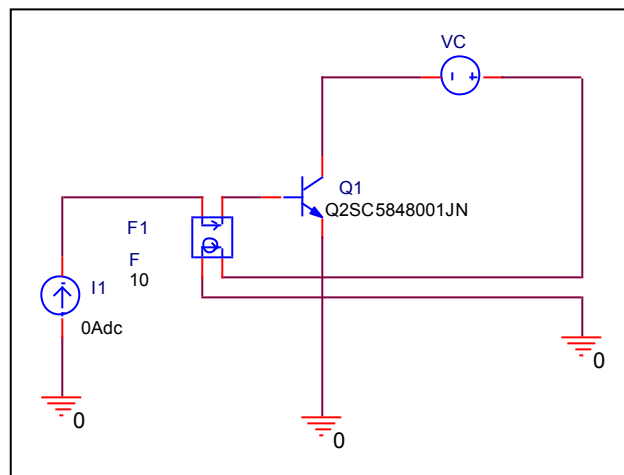
IC(A)	VCE(sat)		Error(%)
	Measurement	Simulation	
0.01	0.0616	0.064681	5.00
0.02	0.0816	0.081341	-0.32
0.05	0.1448	0.139916	-3.37
0.1	0.25	0.254772	1.91

$V_{BE(Sat)}-I_C$ Characteristics

Circuit Simulation Result

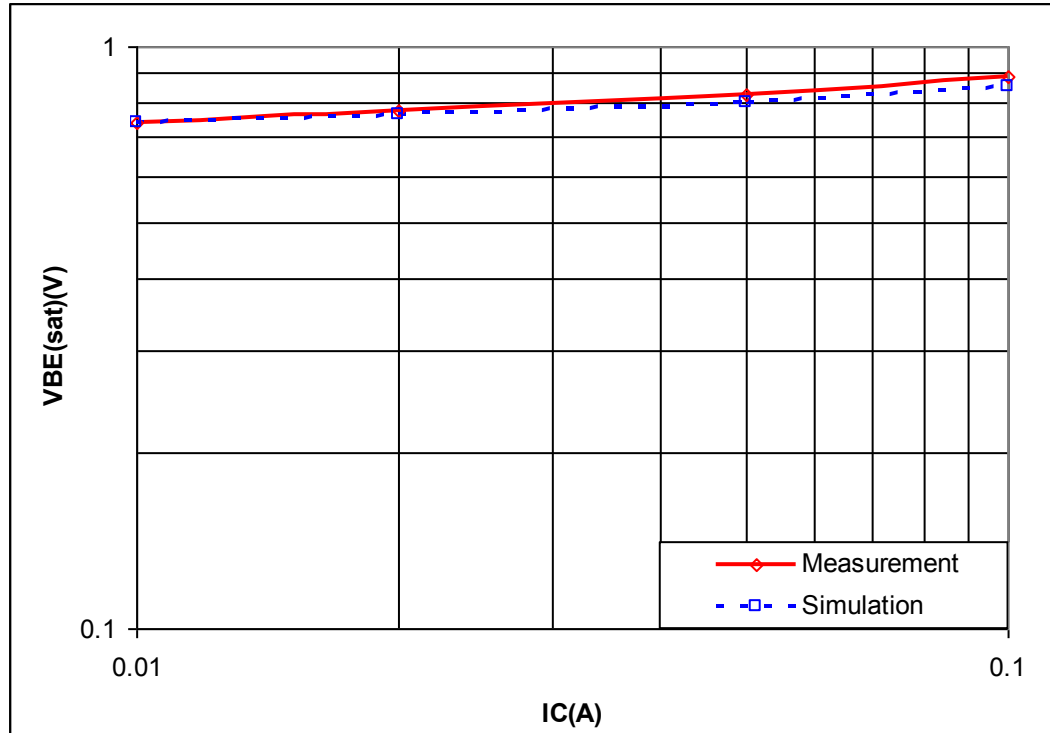


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

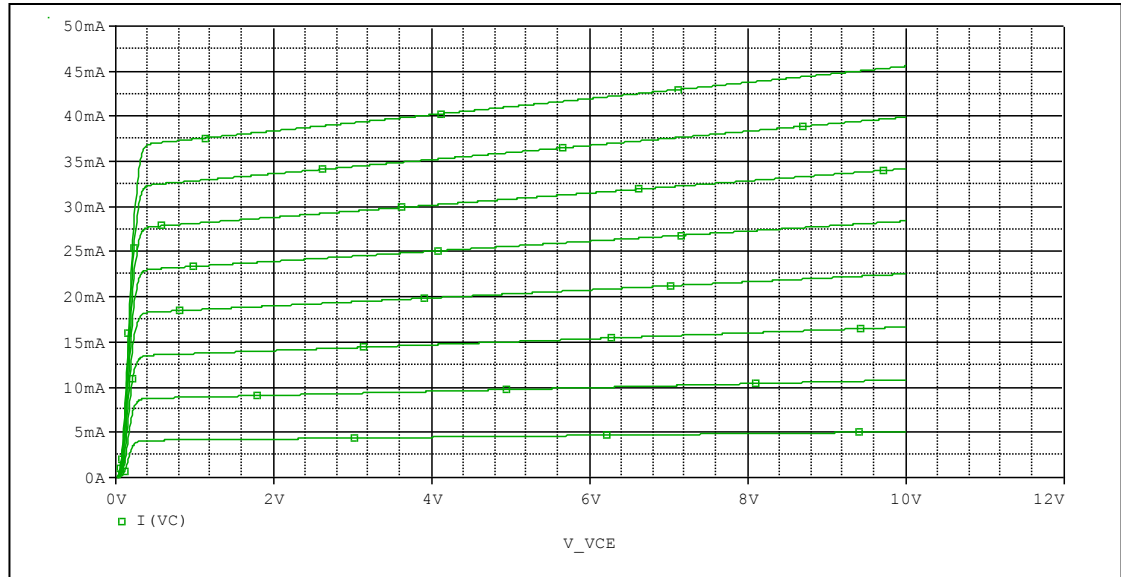


Simulation Result

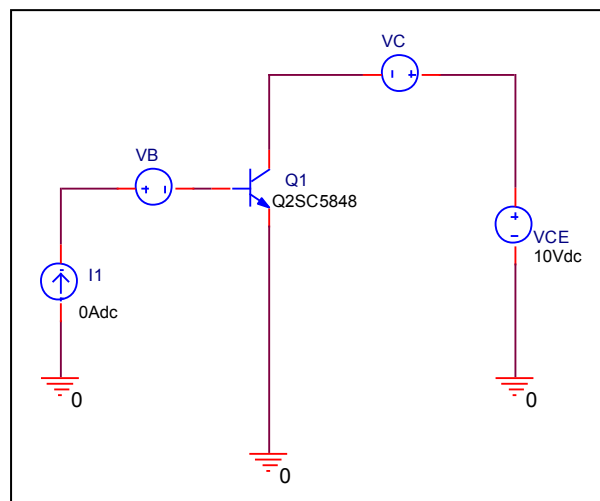
IC(A)	VBE(sat)		Error(%)
	Measurement	Simulation	
0.01	0.74	0.741154	0.16
0.02	0.774	0.764276	-1.26
0.05	0.83	0.802777	-3.28
0.1	0.89	0.852871	-4.17

Output Characteristics

Circuit Simulation Result

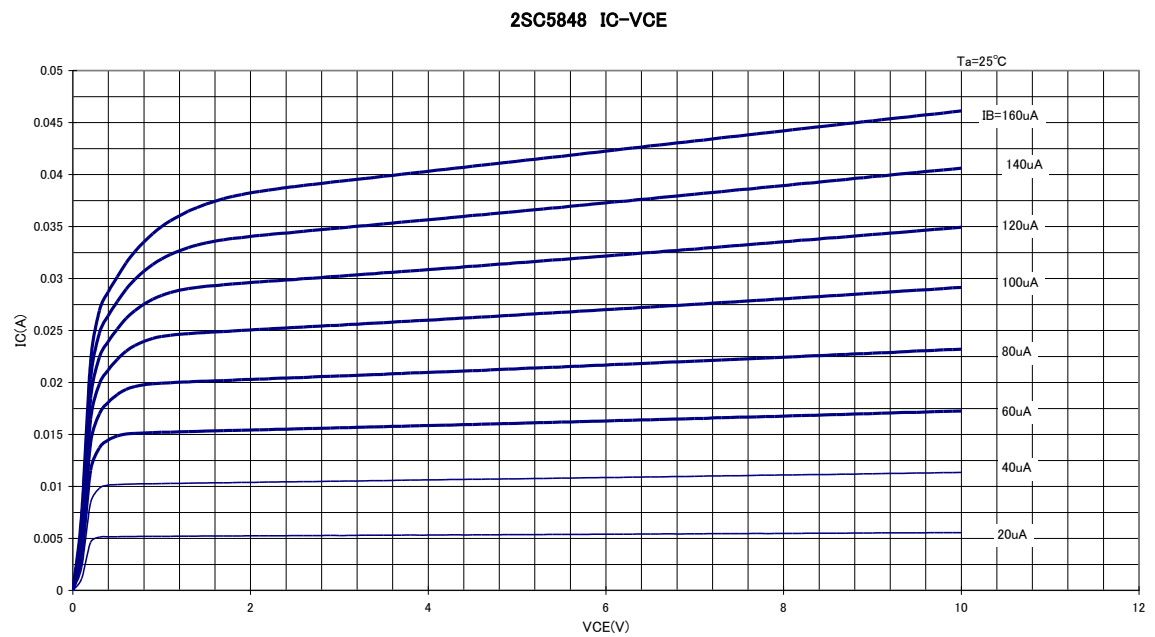


Evaluation Circuit



Output Characteristics

Reference



Semiconductor Company, Matsushita Electric Industrial Co., Ltd.